Bidirectional Discrete TVS Diode, General Purpose Surge Protection





Note: This package image is for example and reference only. for detail package drawing, please refer to the package section in this datasheet.

Pinout



Functional Block Diagram



Description

The AQ1205-01ETG bidirectional TVS is fabricated in a proprietary silicon avalanche technology. These diodes provide a high ESD (electrostatic discharge) protection level for electronic equipment. The AQ1205-01ETG TVS can safely absorb repetitive ESD strikes of ± 30 kV (contact and air discharge as defined in IEC 61000-4-2) without any performance degradation. In addition, it can safely dissipate a 7A 8/20µs surge event as defined in IEC 61000-4-5, 2nd Edition.

Features

- ESD, IEC 61000-4-2, ±30kV contact, ±30kV air
- EFT, IEC 61000-4-4, 40A (5/50ns)
- Surge tolerance, IEC 61000-4-5, 2nd Edition, 7A (8/20µs)
- ESD, ISO 10605, 330pF 330Ω, ±30kV contact, ±30kV air
- Low leakage current of 20nA (MAX) at 5V
- Halogen-free, lead-free and RoHS compliant
- Moisture Sensitivity Level (MSL -1)
- AEC-Q101 Qualified and PPAP capable

Applications

- Switches / Buttons
- Test Equipment / Instrumentation
- Point-of-Sale Terminals
- Medical Equipment
- Notebooks / Desktops / Servers
- Computer Peripherals
- Battery
- Automotive





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Absolute Maximum Ratings

Symbol	Parameter	Value	Units
I _{PP}	Peak Current (t _p =8/20µs)	7	А
T_{OP}	Operating Temperature	-40 to 150	°C
T_{STOR}	Storage Temperature	-55 to 150	°C

Caution: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the component. This is a stress only rating and operation of the component at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Electrical Characteristics (T_{OP}=25°C)

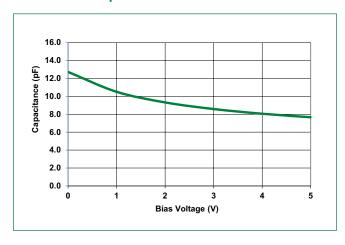
Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Reverse Standoff Voltage	V_{RWM}	$I_R = 1\mu A$			5	V
Breakdown Voltage	$V_{\mathtt{BR}}$	I _R =1mA	5.3	5.5		V
Reverse Leakage Current	I _{LEAK}	V _R =5V		1	20	nA
Clamp Voltage ¹	V _c	$I_{pp} = 7A$, $t_p = 8/20 \mu s$		10		V
Dynamic Resistance ²	R _{DYN}	TLP, t _p =100ns		0.17		Ω
ESD Withstand Voltage ¹	V _{ESD}	IEC 61000-4-2 (Contact Discharge)	±30			kV
		IEC 61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance ¹	C _{IO-GND}	Reverse Bias=5V, f=1MHz		7	9	pF

Note:

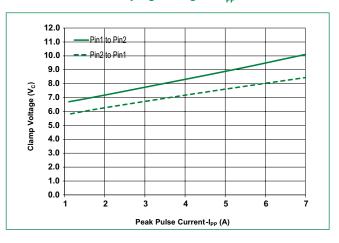
1. Parameter is guaranteed by design and/or component characterization.

2.Transmission Line Pulse (TLP) with 100ns width, 0.2ns rise time, and average window t1=70ns to t2= 90ns

Capacitance vs Reverse Bias



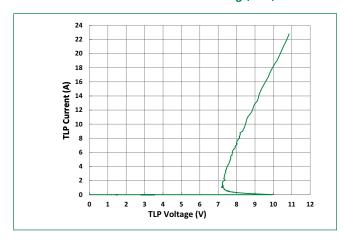
Clamping Voltage vs Ipp



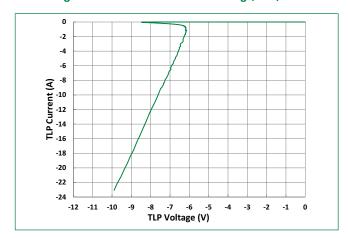


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Positive Transmission Line Pulsing (TLP) Plot



Negative Transmission Line Pulsing (TLP) Plot



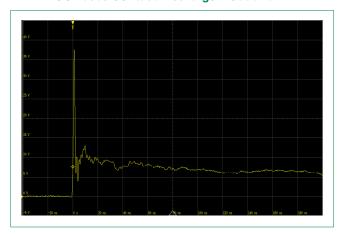
IEC 61000-4-2 +8 kV Contact ESD Clamping Voltage



IEC 61000-4-2 -8 kV Contact ESD Clamping Voltage



ISO 10605 Contact Discharge Plot at +8 kV



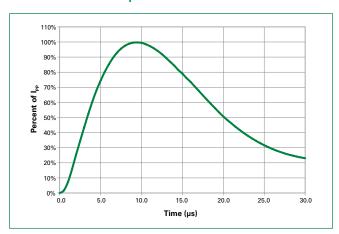
ISO 10605 Contact Discharge Plot at -8 kV





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8/20µs Pulse Waveform



Soldering Parameters

Reflow Condition		Pb – Free assembly	
Pre Heat	-Temperature Min (T _{s(min)})	150°C	
	-Temperature Max (T _{s(max)})	200°C	
	-Time (min to max) (t _s)	60 – 120 secs	
Average ramp up rate (Liquidus) Temp (T_L) to peak		3°C/second max	
T _{S(max)} to T _L - Ramp-up Rate		3°C/second max	
Reflow	-Temperature (T _L) (Liquidus)	217°C	
	-Temperature (t _L)	60 - 150 seconds	
Peak Temperature (T _p)		260 ^{+0/-5} °C	
Time within 5°C of actual peak Temperature (tp)		30 seconds	
Ramp-down Rate		6°C/second max	
Time 25°C to peak Temperature (T _p)		8 minutes Max.	
Do not exceed		260°C	

Ordering Information

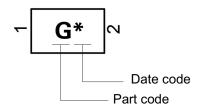
Part Number	Package	Min. Order Qty.
AQ1205-01ETG	SOD882	10,000

T_P Ramp-up T_{S(max)} T_{S(min)} Preheat T_{S(min)} T_{S(min)}

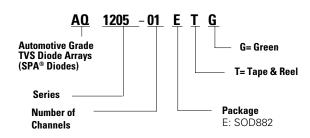
Product Characteristics

Lead Plating	Matte Tin
Lead material	Copper Alloy
Substrate Material	Silicon
Body Material	Molded Compound
Flammability	UL Recognized compound meeting flammability rating V-0

Part Marking System



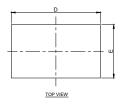
Part Numbering System

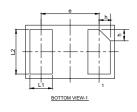




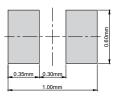
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Package Dimensions — SOD882







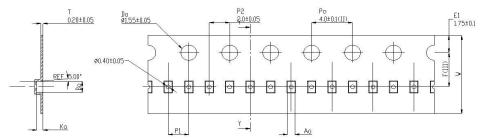


Recommended Soldering Pattern

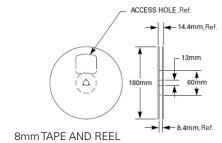
Drawing# : E03-B

SOD882 Symbol Millimeters Inches Min Тур Max Min Тур Max 0.50 0.40 0.55 0.016 0.020 0.022 Α Α1 0.00 0.02 0.05 0.000 0.001 0.002 L1 0.20 0.25 0.30 0.008 0.010 0.012 0.45 0.50 0.018 0.020 0.022 L2 0.55 D 0.95 1.00 1.05 0.037 0.039 0.041 Ε 0.55 0.60 0.65 0.022 0.024 0.026 0.65 BSC 0.026 BSC 0.07 0.12 0.17 0.003 0.005 0.007 h

Embossed Carrier Tape & Reel Specification — SOD882



Symbol	Millimeters
A0	0.70+/-0.045
В0	1.10+/-0.045
K0	0.65+/-0.045
F	3.50+/-0.05
P1	2.00+/-0.10
w	8.00 + 0.30 -0.10



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